Publication List

Journal Publication

 A. Sandupatla, S. Arulkumaran, G. I. Ng, K. Ranjan, M. Deki, S. Nitta, Y. Honda and a. H. Amano, "GaN drift-layer thickness effects in vertical Schottky barrier diodes on free-standing HVPE GaN substrates," *AIP Advances*, vol. 9, p. 045007, 2019.

Conference Publications

- A. Sandupatla, S. Arulkumaran, G. I. Ng, K. Ranjan, M. Deki, S. Nitta, H. Amano, "Effect of GaN Drift Layer Thicknesses in vertical Schottky Barrier Diodes on Free-standing GaN substrate," Solid State Devices and Materials (SSDM), Tokyo, Japan 239 (2018).
- S. Abhinay; S. Arulkumaran; G.I. Ng; K. Ranjan; M. Deki; S. Nitta; Y. Honda; H. Amano, "Effects of Drift Layer Thicknesses in Reverse Conduction Mechanism on Vertical GaN-on-GaN SBDs grown by MOCVD," Electron Devices Technology and Manufacturing Conference (EDTM), Singapore (2019). DOI: 10.1109/EDTM.2019.8731215
- 3. S. Abhinay; S. Arulkumaran; G.I. Ng; K. Ranjan; M. Deki; S. Nitta; Y. Honda; H. Amano, "Enhanced breakdown voltage in vertical Schottky diodes on compensated GaN drift layer grown on free-standing GaN," International Conference on Nitride Semiconductors (ICNS-13), Bellevue, USA (2019)